

## I. INTRODUCTION

**T**HIS document serves as a starting template for writing IEEE-trans. paper in NCTU, RFVLIS-Lab.

### A. First Time Usa of Latex

- 1) Download Miktex, and open package manager. Remember to synchronize package list.
- 2) *Use package* MANAGER TO install the following packages:
  - All IEEE transactions/bibtex packages. (the **ieee-tran**, and **biblatex-ieee** package)
  - **Textcomp**: support some symbols. (the **was** package)
  - **amsmath**: support some maths.
  - **Subfiles**: support independent compilable subfiles .tex structure as used in this template.
  - **dblfloatfix**: fixes double column figures ordering problems. (**dblfloatfix** package.)

### B. Specialized Semiconductor Process

- 1 Some forwords about why needs a rectifier?.
- 2 Focus on introduction of several representative topologies.
- 3 Bring up the the later sections.

### C. Equation Templates

In all of the following approaches, a gate DC bias  $V_{g,bias}$  is introduced as in Eq. XXXX.

$$V_{out} = N(V_{RF,Peak} - V_{th} + V_{gs,bias}). \quad (1)$$

### D. Table Templates

### E. Inductive Peaking Approach

### F. Other Approaches

TABLE I  
SUMMARY OF THE UHF RF-TO-DC RECTIFIER PERFORMANCE.

Specification	This work	A	B	C
Frequency(MHz)	900	950	915	915
Technology	0.28 $\mu$ m thick-gate oxide CMOS in 65nm process	0.35 $\mu$ m	90nm	0.2 $\mu$ m
PCE@Output power	27.97% @ 19.3mW	15.1% @ 0.6 $\mu$ W	11% @ 13.1 $\mu$ W	71.5% @ 0.285mW
Number of stage / type of the rectifier	5/half-wave	1 (six stacks) / full-wave	17/half-wave	1/full-wave
Chip area	0.442mm <sup>2</sup>	0.104mm <sup>2</sup>	0.19mm <sup>2</sup>	0.133mm <sup>2</sup>